

**SILICON PHOTO DIODES**
**BL-L3522PD**
**Features:**

- 5.1\*3.0\*7.4mm SILICON PHOTO DIODES
- Choice of various viewing angles.
- Diffused and Water clear lens are available.
- Fast response time.
- High photo sensitivity.
- Small junction capacitance.
- The epoxy package itself is an IR filter, spectrally matched to GaAs or GaAlAs IR emitter.


**RoHS Compliance**
**Applications:**

- High speed photo detector
- Camera
- Infrared remote controller for TVs VCR, audio equipment, air conditioner, etc.

**Absolute Maximum Ratings at Ta=25°C**

Parameter	Symbol	Rating	Unit
Power Dissipation	$P_d$	150	mW
Reverse Voltage	$V_R$	35	V
Operation Temperature	$T_{OPR}$	-40 to +80	°C
Storage Temperature	$T_{STG}$	-40 to +85	°C
Lead Soldering Temperature	TSOL	Max.260±5°C for 3 sec Max. (1.6mm from the base of the epoxy bulb)	°C

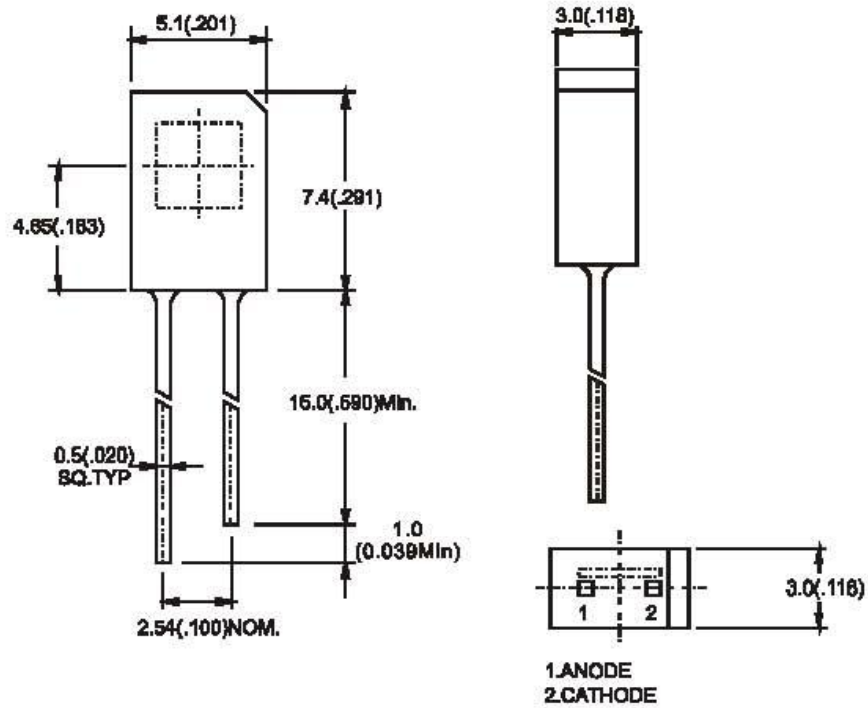
**Electronic Optical Characteristics at Ta=25°C**

Items	Symbol	Min.	Typ.	Max.	Unit	Condition
Wavelength of Peak Sensitivity	$\lambda_p$	-	940	-	nm	-
Open Circuit Voltage	$V_{OC}$	-	0.35	-	V	H=5mW/cm <sup>2</sup> $\lambda_p$ =940nm
Short Circuit Current	$I_{SC}$	-	75	-	uA	
Reverse Current	$I_L$	-	120	-	uA	H=5mW/cm <sup>2</sup> $\lambda_p$ =940nm $V_R$ =5V
Reverse Current	$I_D$	-	5	30	nA	H=0mW/cm <sup>2</sup> $V_R$ =10V
Reverse down Voltage	$V_{BR}$	35	170	-	V	H=0mW/cm <sup>2</sup> $I_R$ =100uA
Viewing angle	$2\theta/2$	-	35	-	Deg	
Rise/Fall Time	$T_r/T_f$	-	50/50	-	nS	$R_L$ =1000 $\Omega$ , $V_R$ =10V

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□ **Package configuration & Internal circuit diagram**



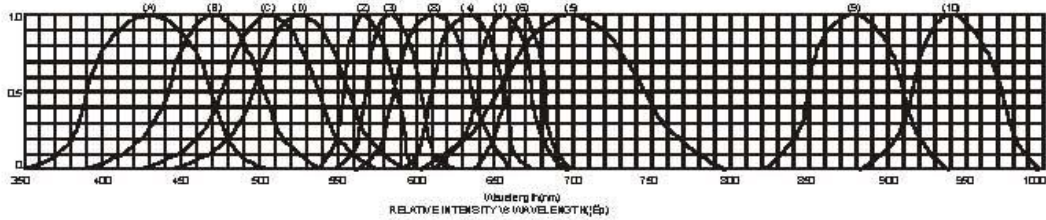
Notes:

1. All dimensions are in millimeters (inches)
2. Tolerance is  $\pm 0.25(0.01)$  unless otherwise noted.
3. Specifications are subject to change without notice.

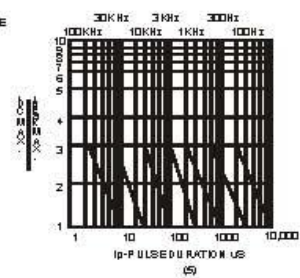
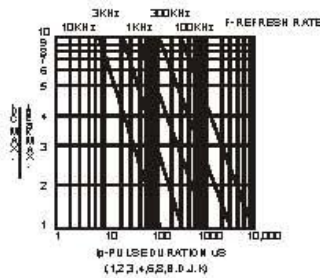
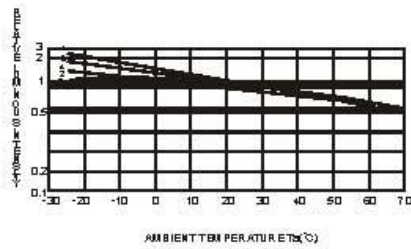
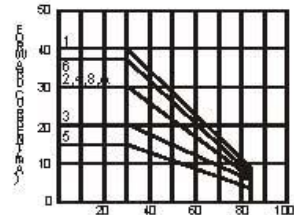
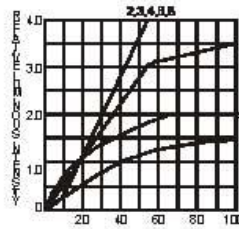
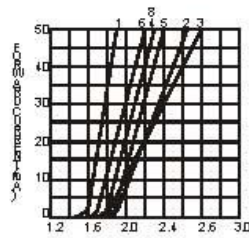
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□ Typical electrical-optical characteristics curves:



- (1) - GaAsP/GaAs 655nm/Red
- (2) - GaP 570nm/Yellow Green
- (3) - GaAsP/GaP 585nm/Yellow
- (4) - GaAsP/GaP 635nm/Orange & Hi-Eff Red
- (5) - GaP 700nm/Bright Red
- (6) - GaAlAs/GaAs 660nm/Super Red
- (8) - GaAsP/GaP 610nm/Super Red
- (9) - GaAlAs 880nm
- (10) - GaAs/GaAs & GaAlAs/GaAs 940nm
- (A) - GaN/SiC 430nm/Blue
- (B) - InGaN/SiC 470nm/Blue
- (C) - InGaN/SiC 505nm/Ultra Green
- (D) - InGaAl/SiC 525nm/Ultra Green



NO TESTS AT 25°C unless otherwise specified